

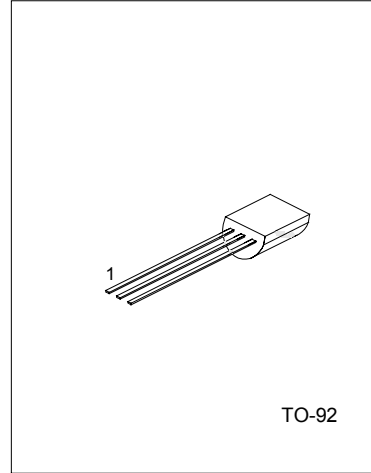
UTC2SA1015

PNP EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY PNP AMPLIFIER TRANSISTOR

FEATURES

- *Collector-Emitter Voltage:
BV_{CEO}=-50V
- *Collector current up to 150mA
- *High hFE linearity
- *Complement to 2SC1815



1:EMITTER 2:COLLECTOR 3: BASE

ABSOLUTE MAXIMUM RATINGS (Ta=25°C ,unless otherwise specified)

| PARAMETER | SYMBOL | RATING | UNIT |
|---------------------------|------------------|------------|------|
| Collector-base voltage | V _{CB0} | -50 | V |
| Collector-emitter voltage | V _{CEO} | -50 | V |
| Emitter-base voltage | V _{EB0} | -5 | V |
| Collector dissipation | P _c | 400 | mW |
| Collector current | I _c | -150 | mA |
| Base current | I _B | -50 | mA |
| Junction Temperature | T _j | 125 | °C |
| Storage Temperature | T _{STG} | -65 ~ +150 | °C |

ELECTRICAL CHARACTERISTICS(Ta=25°C,unless otherwise specified)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--------------------------------------|----------------------|--|-----|------|------|------|
| Collector-base breakdown voltage | BV _{CB0} | I _c =-100μA,I _E =0 | -50 | | | V |
| Collector-emitter breakdown voltage | BV _{CEO} | I _c =-10mA,I _B =0 | -50 | | | V |
| Emitter-base breakdown voltage | BV _{EB0} | I _E =-10μA,I _c =0 | -5 | | | V |
| Collector cut-off current | I _{CB0} | V _{CB} =-50V,I _E =0 | | | -100 | nA |
| Emitter cut-off current | I _{EB0} | V _{EB} =-5V,I _c =0 | | | -100 | nA |
| DC current gain(note) | h _{FE1} | V _{CE} =-6V,I _c =-2mA | 70 | | 400 | |
| | h _{FE2} | V _{CE} =-6V,I _c =-150mA | 25 | | | |
| Collector-emitter saturation voltage | V _{CE(sat)} | I _c =-100mA,I _B =-10mA | | -0.1 | -0.3 | V |
| Base-emitter saturation voltage | V _{BE(sat)} | I _c =-100mA,I _B =-10mA | | | -1.1 | V |
| Current gain bandwidth product | f _t | V _{CE} =-10V,I _c =-1mA | 80 | | | MHz |
| Output capacitance | C _{ob} | V _{CB} =-10V,I _E =0,f=1MHz | | 4.0 | 7.0 | pF |
| Noise Figure | NF | I _c =-0.1mA,V _{CE} =-6V R _G =1kΩ,f=100Hz | | 0.5 | 6 | dB |

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CLASSIFICATION OF hFE1

| | | |
|-------|---------|---------|
| RANK | Y | G |
| RANGE | 120-240 | 200-400 |

TYPICAL CHARACTERISTIC CURVES

